

**DUAL SURFACE MOUNT SCHOTTKY**

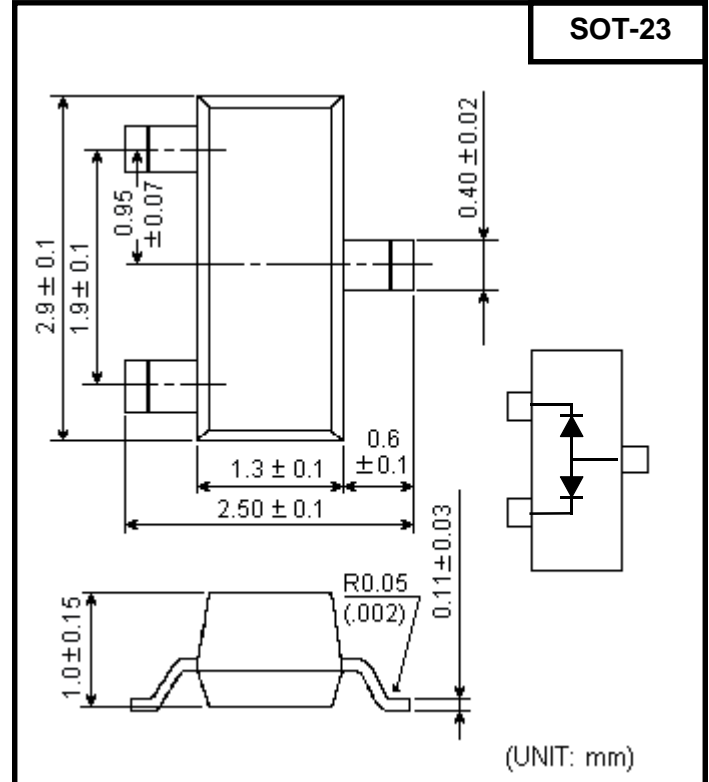
**Absolute Maximum Ratings per Diode (Ta=25°C)**

| Items                           | Symbol           | Ratings    | Unit |
|---------------------------------|------------------|------------|------|
| Reverse Voltage                 | VR               | 30         | V    |
| Power Dissipation *             | P <sub>TOT</sub> | 300        | mW   |
| Forward Voltage<br>@ If = 100mA | VF               | 1.0        | V    |
| Forward Current                 | IF               | 200        | mA   |
| Junction Temp.                  | T <sub>J</sub>   | -55 to 125 | °C   |
| Storage Temp.                   | T <sub>STG</sub> | -55 to 150 | °C   |

**Mechanical Data**

| Items       | Materials      |
|-------------|----------------|
| Package     | SOT-23         |
| Lead Frame  | 42 Alloy       |
| Lead Finish | Solder Plating |
| Bond Wire   | Au             |
| Mold Resin  | Epoxy          |
| Chip        | Silicon        |

**Dimensions**



**Electrical Characteristics per diode (Ta=25°C)**

| Ratings  | Symbol | Ratings                          | Unit |
|--|--------|----------------------------------|------|
| Minimum Repetitive Peak Reverse Voltage  | VRRM   | 30                               | V    |
| Maximum Repetitive Peak Forward Current  | IFRM   | 300                              | mA   |
| Maximum Forward Voltage<br>IF= 100uA<br>IF= 1mA<br>IF= 10mA<br>IF= 30mA<br>IF= 100mA | VF     | 240<br>320<br>400<br>500<br>1000 | mV   |
| Maximum Reverse Current<br>VR= 25V   | IR     | 2.0                              | uA   |
| Maximum Junction Capacitance<br>VR= 1V, f= 1MHz                                      | Cj     | 15                               | pF   |
| Maximum Reverse Recovery Time<br>IF= 10mA, IR= 10mA, IRR= 1mA, RL= 100W              | trr    | 5                                | ns   |
| Thermal Resistance*  | Rθjc   | 430                              | °C/W |

\* (Mounted on a 10x8x0.6mm ceramic substrate)